

## 650V N-ch Planar MOSFET

$BV_{DSS}$	$R_{DS(ON),Typ.}$	$I_D$
650V	1.2Ω	7.0A

### General Features

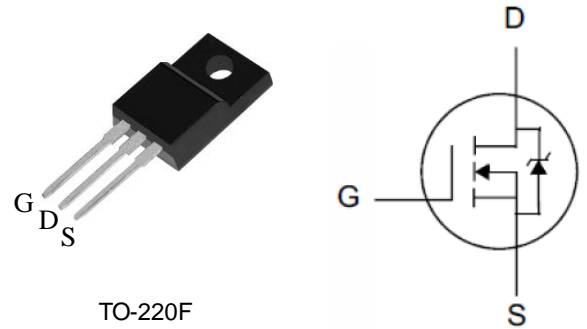
- RoHS Compliant
- $R_{DS(ON),typ.}=1.2\ \Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

### Applications

- Adaptor
- Charger
- SMPS Standby Power

### Ordering Information

Part Number	Package
SK07N65B-TF	TO-220F



### Absolute Maximum Ratings

$T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	SK07N65B-TF	Unit
$V_{DSS}$	Drain-to-Source Voltage	650	V
$V_{GSS}$	Gate-to-Source Voltage	±30	
$I_D$	Continuous Drain Current	7.0	A
$I_{DM}$	Pulsed Drain Current at $V_{GS}=10V$	28	
$E_{AS}$	Single Pulse Avalanche Energy	550	mJ
$P_D$	Power Dissipation	42	W
	Derating Factor above $25^\circ\text{C}$	0.34	W/°C
$T_L$ $T_{PAK}$	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	°C
$T_J$ & $T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

### Thermal Characteristics

Symbol	Parameter	SK07N65B-TF	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.98	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	

## Electrical Characteristics

### OFF Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	650	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	1	$\mu A$	$V_{DS}=650V, V_{GS}=0V$
		--	--	100		$V_{DS}=520V, V_{GS}=0V, T_J=125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Leakage Current	--	--	+100	$nA$	$V_{GS}=+30V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

### ON Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	1.2	1.40	$\Omega$	$V_{GS}=10V, I_D=3.0A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	11	--	S	$V_{DS}=30V, I_D=3.5A$

### Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$C_{iss}$	Input Capacitance	--	1120	--	$pF$	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$
$C_{rss}$	Reverse Transfer Capacitance	--	10	--		
$C_{oss}$	Output Capacitance	--	90	--		
$Q_g$	Total Gate Charge	--	20	--	$nC$	$V_{DD}=325V, I_D=7A, V_{GS}=0 \text{ to } 10V$
$Q_{gs}$	Gate-to-Source Charge	--	5	--		
$Q_{gd}$	Gate-to-Drain (Miller) Charge	--	5	--		

### Resistive Switching Characteristics

Essentially independent of operating temperature

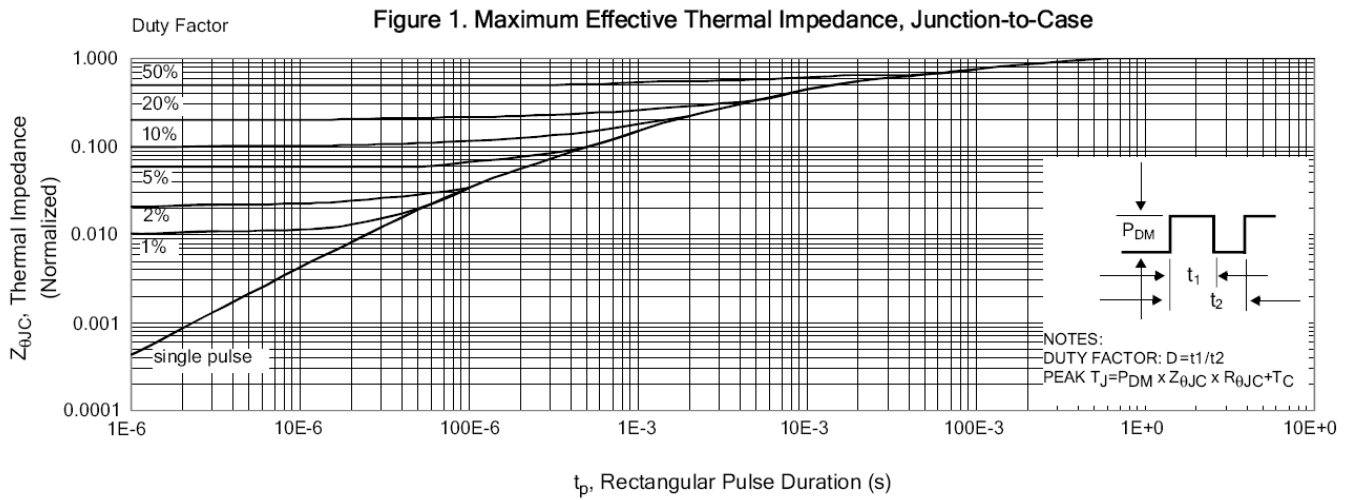
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	12	--	$ns$	$V_{DD}=325V, I_D=7A, V_{GS}=10V, R_g=4.7\Omega$
$t_{rise}$	Rise Time	--	12	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	18	--		
$t_{fall}$	Fall Time	--	10	--		

## Source-Drain Body Diode Characteristics

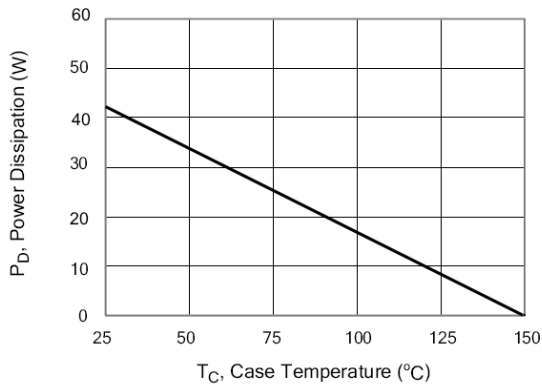
$T_J=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
$I_{SD}$	Continuous Source Current <sup>[2]</sup>	--	--	7.0	A	Integral pn-diode in MOSFET
$I_{SM}$	Pulsed Source Current <sup>[2]</sup>	--	--	28		
$V_{SD}$	Diode Forward Voltage	--	--	1.5	V	$I_S=7\text{A}$ , $V_{GS}=0\text{V}$
$t_{rr}$	Reverse Recovery Time	--	350	--	ns	$V_{GS}=0\text{V}$ $I_F=7\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$
$Q_{rr}$	Reverse Recovery Charge	--	1.1	--	$\mu\text{C}$	

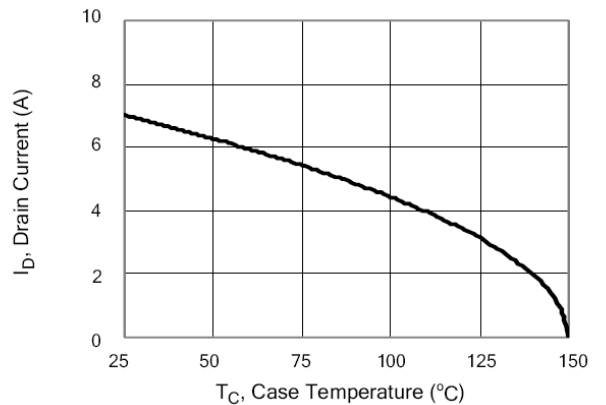
**Note:** [1]  $T_J=+25$  to  $+150$   
 [2] Pulse width $\leq 380\mu\text{s}$ ; duty cycle $\leq 2\%$ .



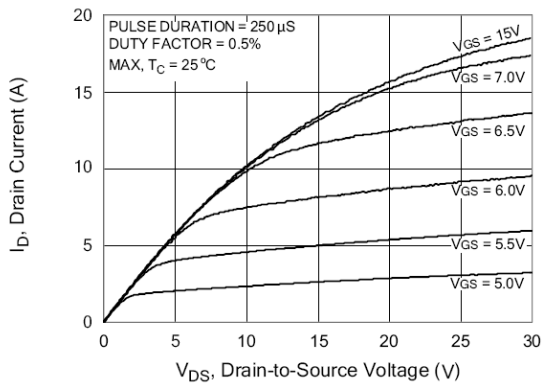
**Figure 2. Maximum Power Dissipation vs Case Temperature**



**Figure 3. Maximum Continuous Drain Current vs Case Temperature**



**Figure 4. Typical Output Characteristics**



**Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current**

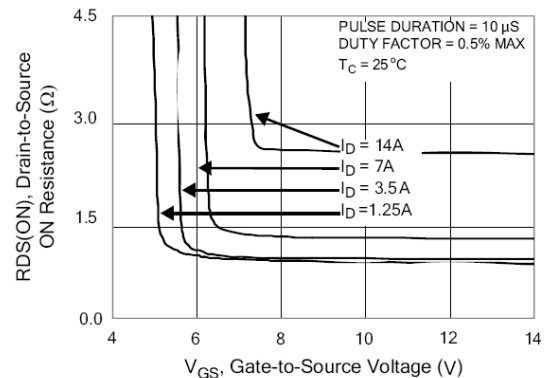


Figure 6. Maximum Peak Current Capability

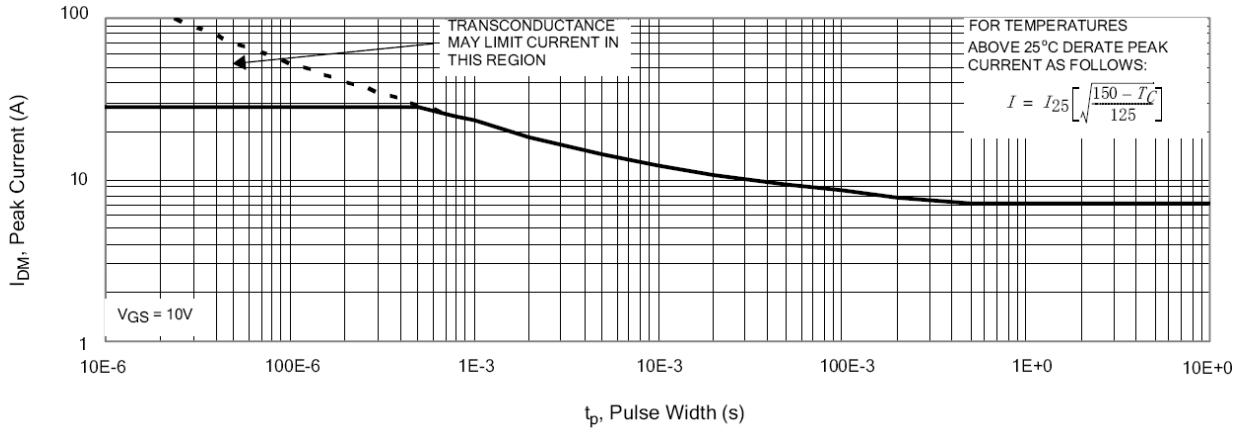


Figure 7. Typical Transfer Characteristics

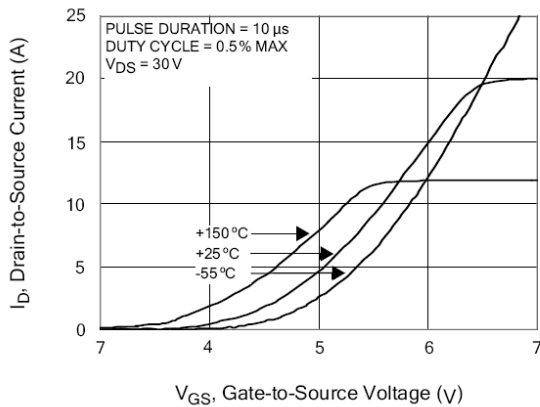


Figure 8. Unclamped Inductive Switching Capability

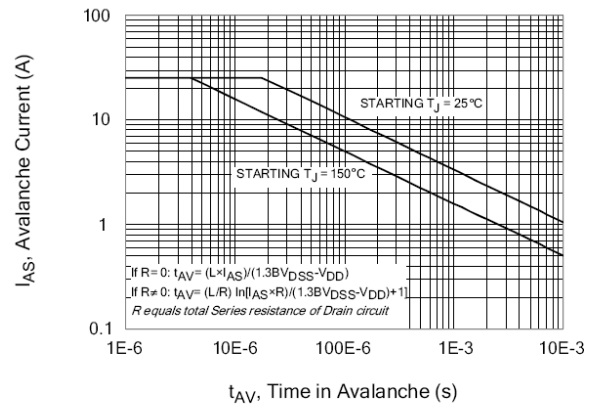


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

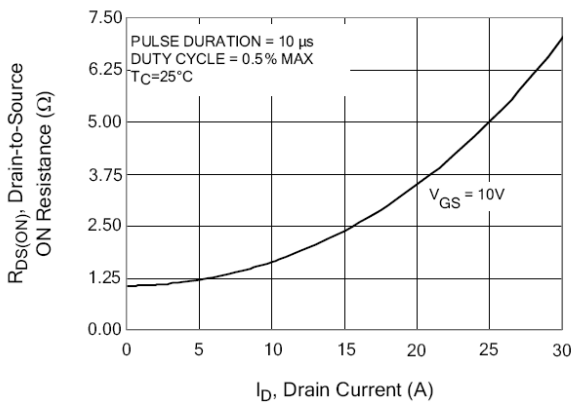


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

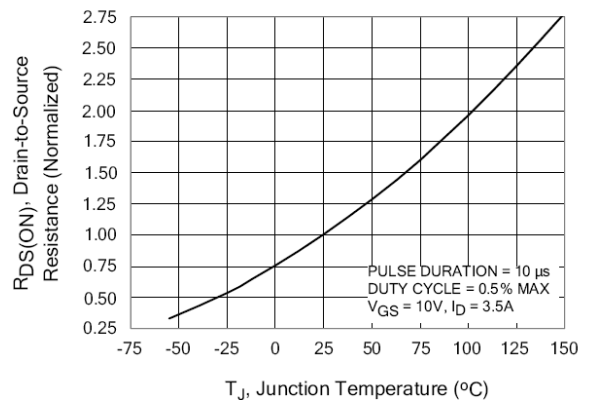


Figure 11. Typical Breakdown Voltage vs Junction Temperature

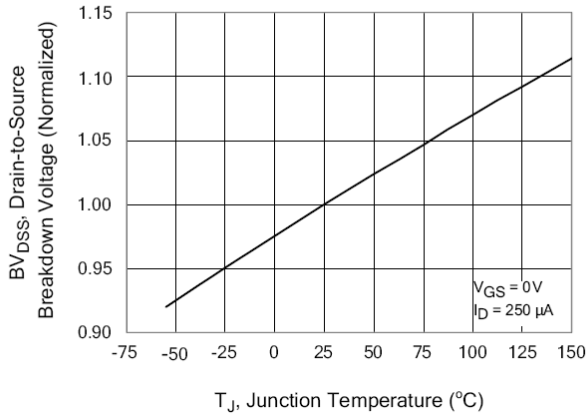


Figure 12. Typical Threshold Voltage vs Junction Temperature

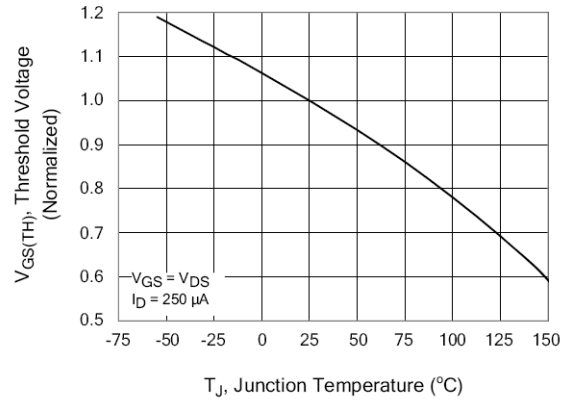


Figure 13. Maximum Safe Operating Area

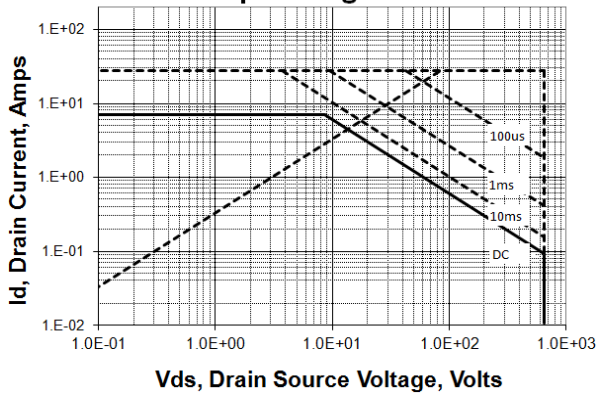


Figure 14. Capacitance vs Vds

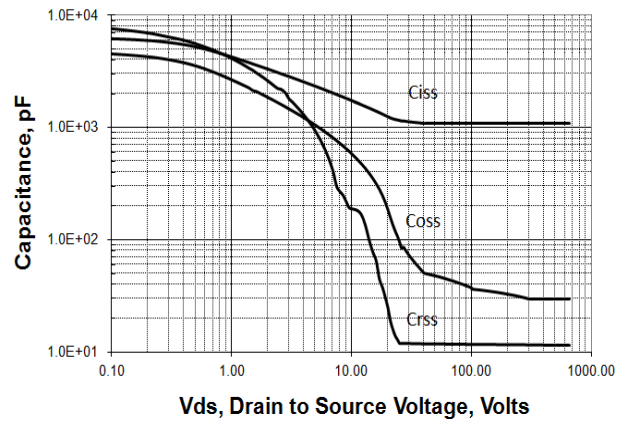


Figure 15. Typical Gate Charge

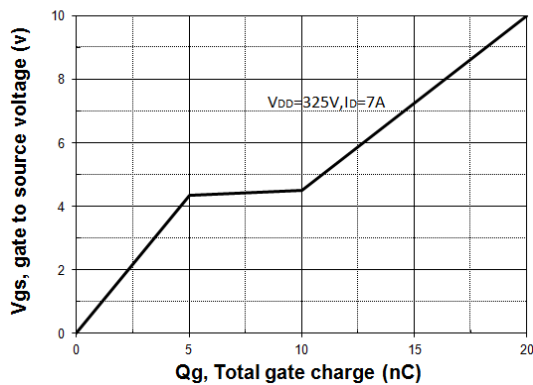
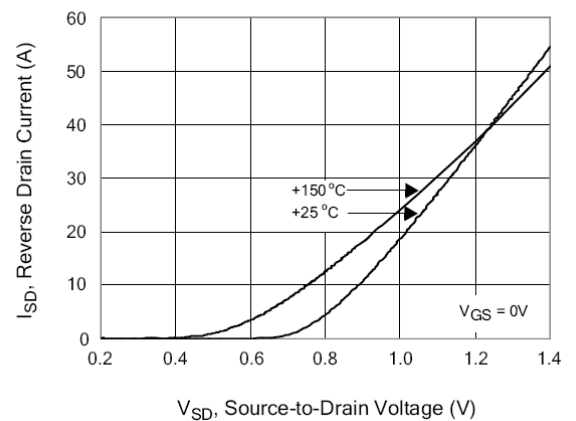


Figure 16. Typical Body Diode Transfer Characteristics



## Test Circuits and Waveforms

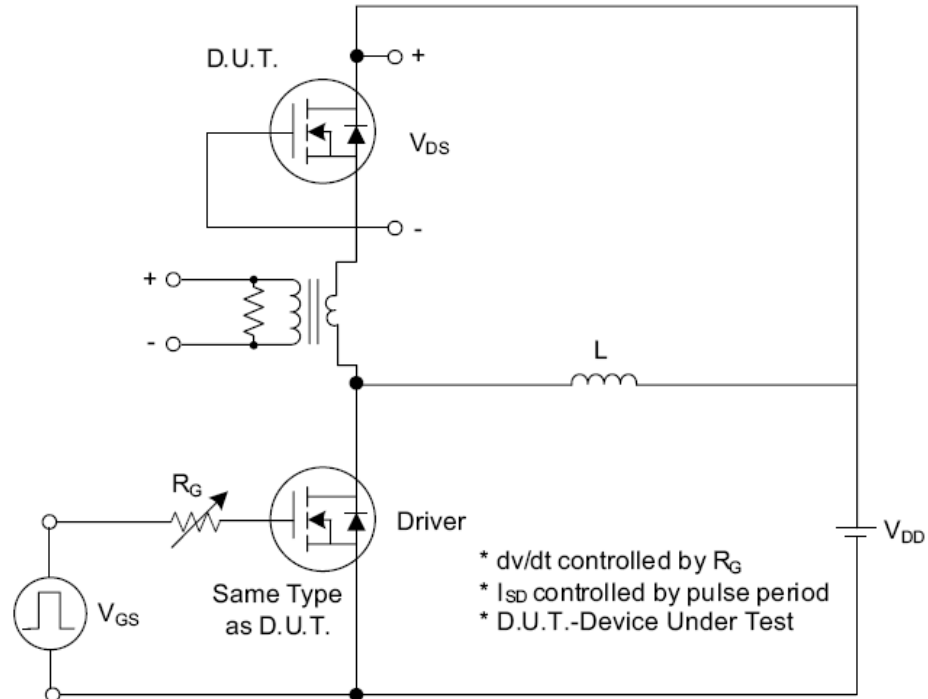


Fig. 1.1 Peak Diode Recovery  $dv/dt$  Test Circuit

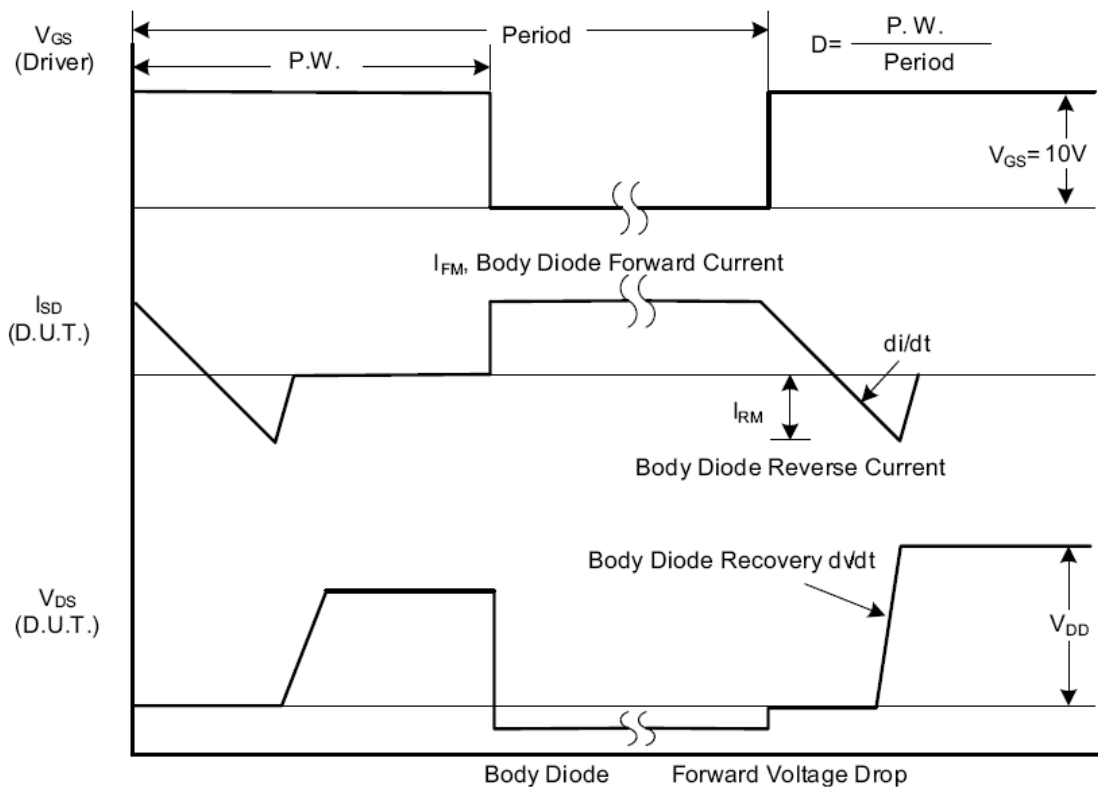


Fig. 1.2 Peak Diode Recovery  $dv/dt$  Waveforms

## Test Circuits and Waveforms (Cont.)

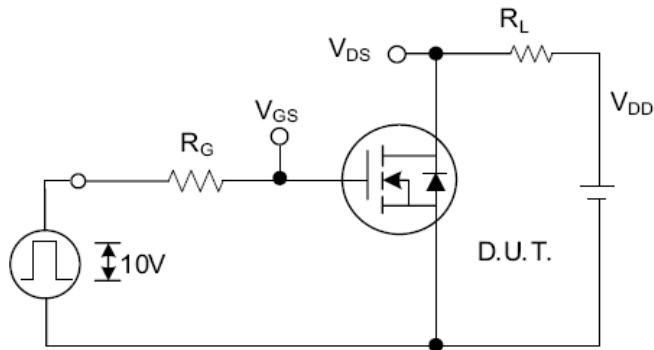


Fig. 2.1 Switching Test Circuit

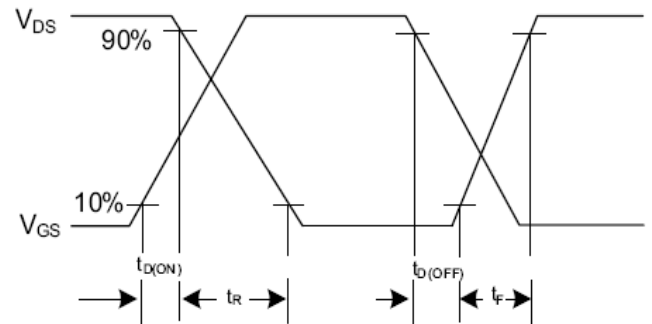


Fig. 2.2 Switching Waveforms

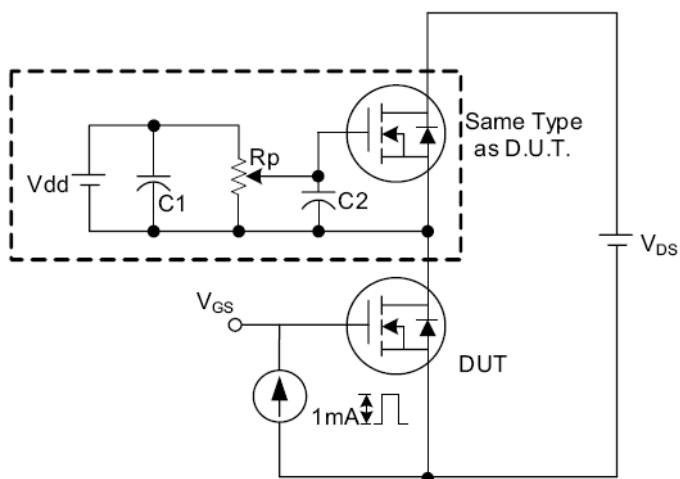


Fig. 3.1 Gate Charge Test Circuit

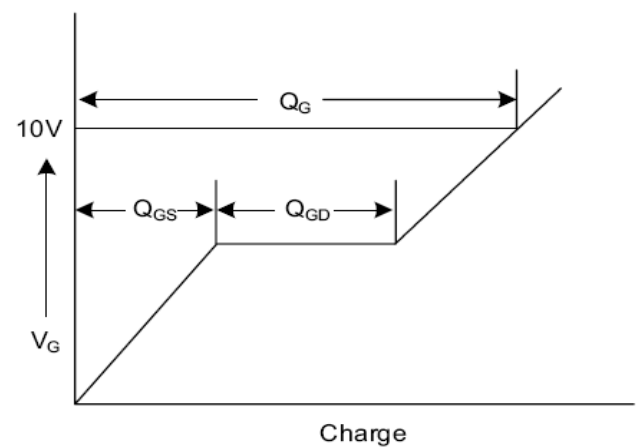


Fig. 3.2 Gate Charge Waveform

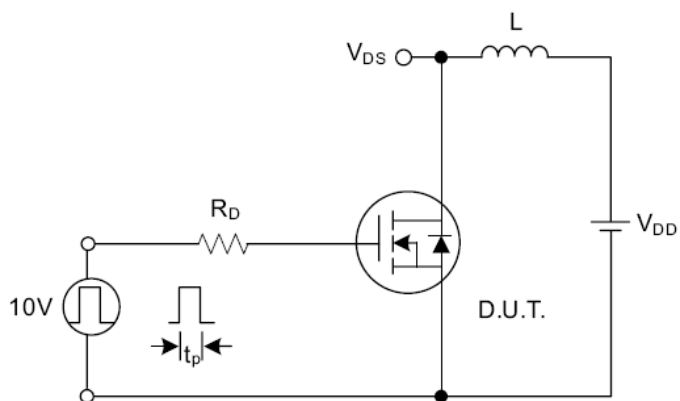


Fig. 4.1 Unclamped Inductive Switching Test Circuit

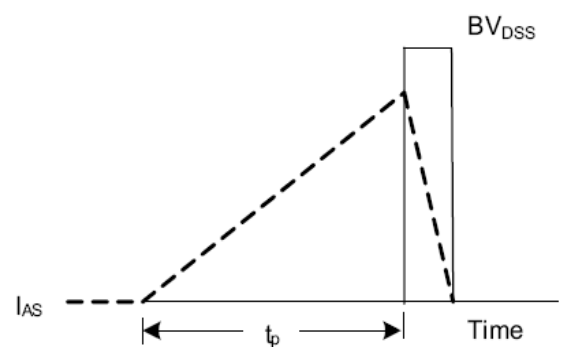


Fig. 4.2 Unclamped Inductive Switching Waveforms



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